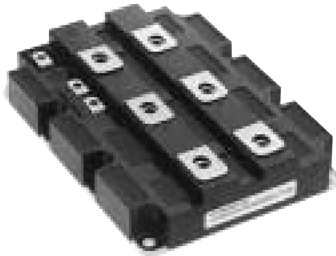
CM800E2Z-66H

HIGH POWER SWITCHING USE
INSULATED TYPE

2nd-Version HVIGBT (High Voltage Insulated Gate Bipolar Transistor) Modules

CM800E2Z-66H

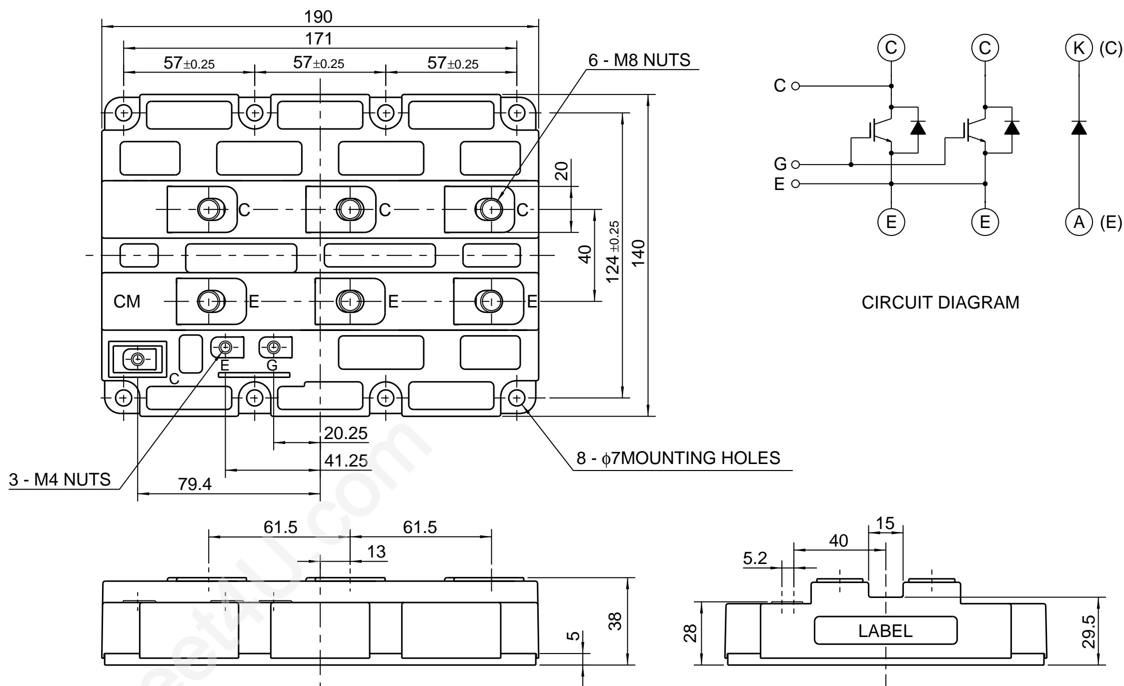


- I_C 800A
- V_{CES} 3300V
- Insulated Type
- 1-elements in a pack (for brake)

APPLICATION

DC choppers, Dynamic braking choppers.

OUTLINE DRAWING & CIRCUIT DIAGRAM — Dimensions in mm



HVIGBT MODULES (High Voltage Insulated Gate Bipolar Transistor Modules)

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MAXIMUM RATINGS (T_j = 25°C)

Symbol	Item	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	V_{GE} = 0V	3300	V
V_{GES}	Gate-emitter voltage	V_{CE} = 0V	±20	V
I_C	Collector current	DC, T_C = 100°C	800	A
I_{CM}		Pulse (Note 1)	1600	A
I_E (Note 2)	Emitter current		800	A
I_{EM} (Note 2)		Pulse (Note 1)	1600	A
P_C (Note 3)	Maximum collector dissipation	T_C = 25°C, IGBT part	10400	W
T_j	Junction temperature	—	–40 ~ +150	°C
T_{stg}	Storage temperature	—	–40 ~ +125	°C
V_{iso}	Isolation voltage	Charged part to base plate, rms, sinusoidal, AC 60Hz 1min.	6000	V
—	Mounting torque	Main terminals screw M8	6.67 ~ 13.00	N·m
		Mounting screw M6	2.84 ~ 6.00	N·m
		Auxiliary terminals screw M4	0.88 ~ 2.00	N·m
—	Mass	Typical value	2.2	kg

ELECTRICAL CHARACTERISTICS (T_j = 25°C)

Symbol	Item	Conditions		Limits			Unit
				Min	Typ	Max	
I_{CES}	Collector cutoff current	V_{CE} = V_{CES}, V_{GE} = 0V		—	—	10	mA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C = 80mA, V_{CE} = 10V		4.5	6.0	7.5	V
I_{GES}	Gate-leakage current	V_{GE} = V_{GES}, V_{CE} = 0V		—	—	0.5	μA
$V_{CE(sat)}$	Collector-emitter saturation voltage	T_j = 25°C	I_C = 800A, V_{GE} = 15V (Note 4)	—	3.80	4.94	V
		T_j = 125°C		—	4.00	—	
C_{ies}	Input capacitance	V_{CE} = 10V, V_{GE} = 0V		—	120	—	nF
C_{oes}	Output capacitance			—	12.0	—	nF
C_{res}	Reverse transfer capacitance			—	3.6	—	nF
Q_G	Total gate charge	V_{CC} = 1650V, I_C = 800A, V_{GE} = 15V		—	5.7	—	μC
$t_{d(on)}$	Turn-on delay time	V_{CC} = 1650V, I_C = 800A, V_{GE1} = V_{GE2} = 15V, R_G = 2.5Ω, Resistive load switching operation		—	—	1.60	μs
t_r	Turn-on rise time			—	—	2.00	μs
$t_{d(off)}$	Turn-off delay time			—	—	2.50	μs
t_f	Turn-off fall time			—	—	1.00	μs
V_{EC} (Note 2)	Emitter-collector voltage	I_E = 800A, V_{GE} = 0V		—	2.80	3.64	V
t_{rr} (Note 2)	Reverse recovery time	I_E = 800A, di_E / dt = –1600A / μs		—	—	1.40	μs
Q_{rr} (Note 2)	Reverse recovery charge			—	270	—	μC
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, IGBT part		—	—	0.012	K/W
$R_{th(j-c)R}$		Junction to case, FWDi part		—	—	0.024	K/W
$R_{th(c-f)}$	Contact thermal resistance	Case to fin, conductive grease applied (Per 2/3 module)		—	0.008	—	K/W
V_{FM}	Forward voltage	I_F = 800A, Clamp diode part		—	3.00	3.90	V
t_{rr}	Reverse recovery time	I_F = 800A, di_F / dt = –1600A / μs, Clamp diode part		—	—	1.40	μs
Q_{rr}	Reverse recovery charge			—	270	—	μC
$R_{th(j-c)}$	Thermal resistance	Junction to case, Clamp diode part		—	—	0.024	K/W
$R_{th(c-f)}$	Contact thermal resistance	Case to fin, conductive grease applied (Per 1/3 module)		—	0.008	—	K/W

Note 1. Pulse width and repetition rate should be such that the device junction temp. (T_j) does not exceed T_{jmax} rating.
2. I_E, V_{EC}, t_{rr}, Q_{rr} & die/dt represent characteristics of the anti-parallel, emitter to collector free-wheel diode.
3. Junction temperature (T_j) should not increase beyond 150°C.
4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

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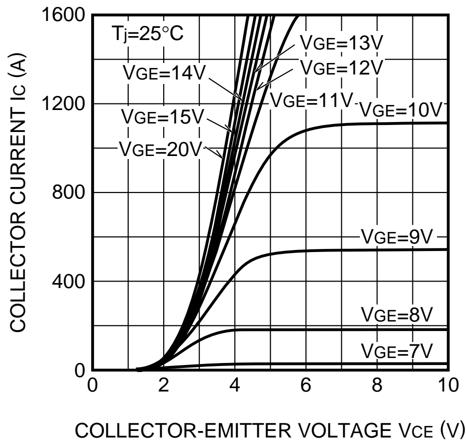
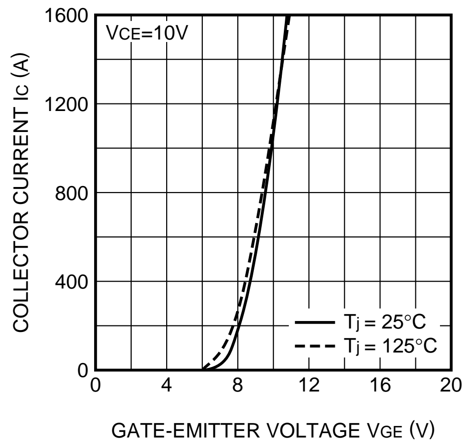
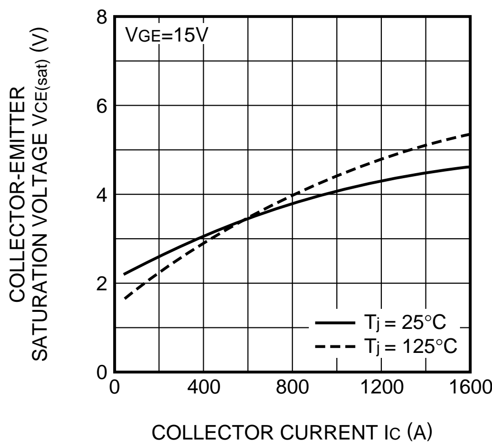
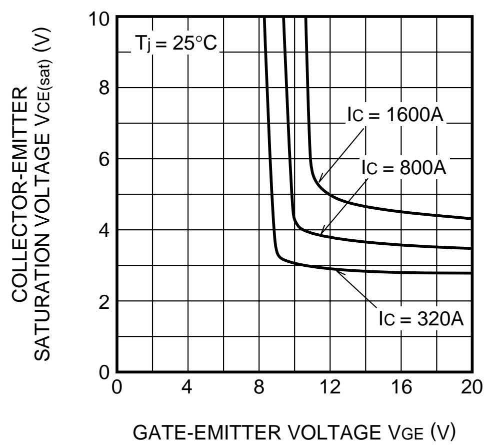
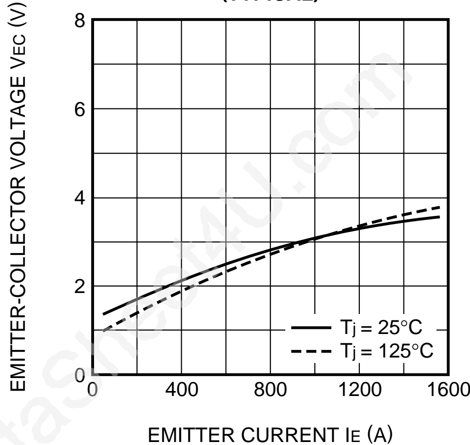
PERFORMANCE CURVES

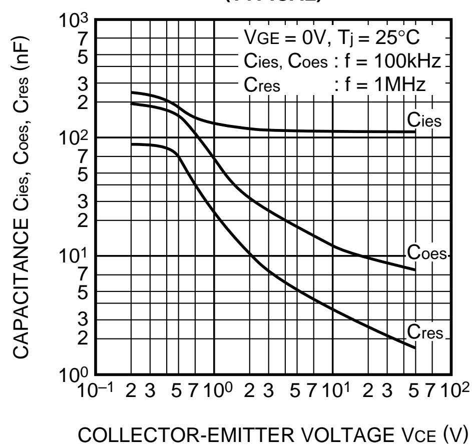


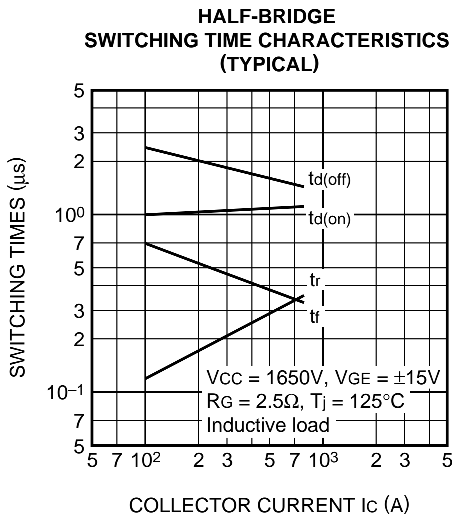


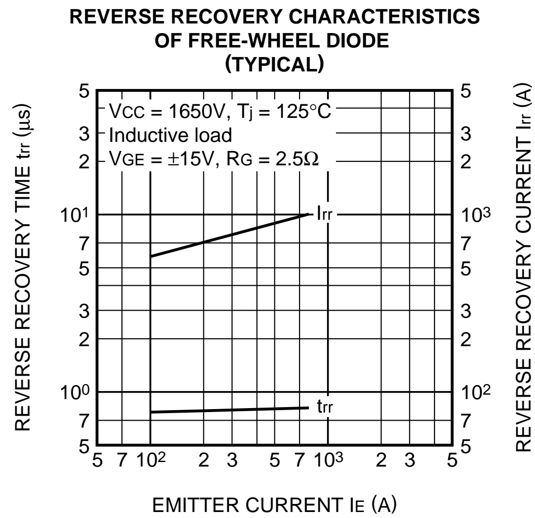


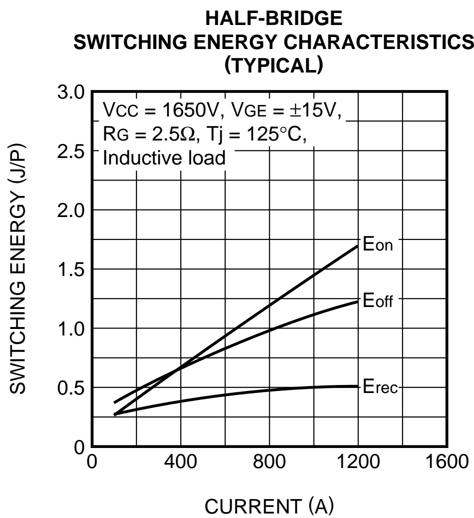


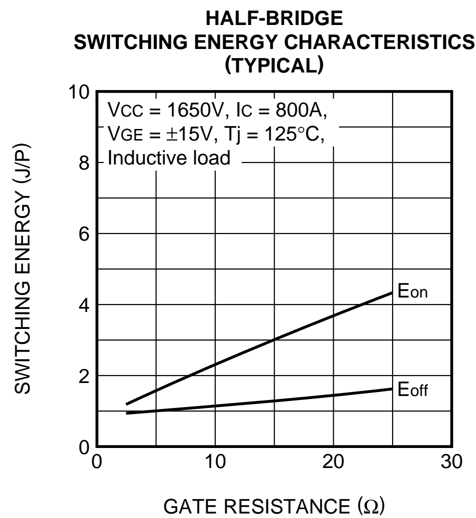


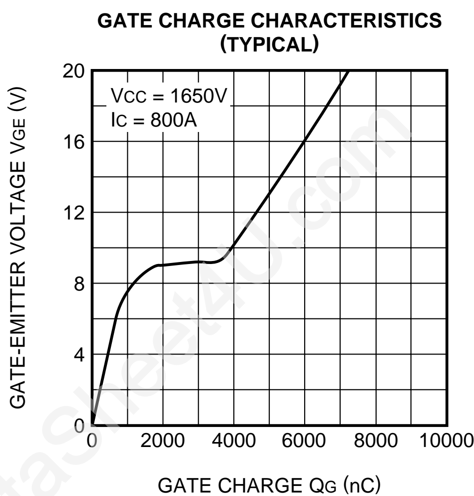


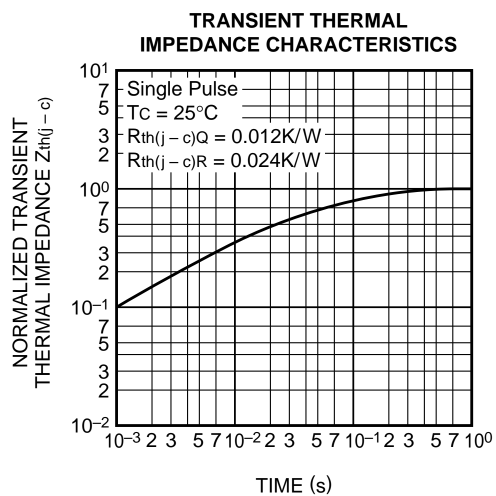

HALF-BRIDGE
SWITCHING TIME CHARACTERISTICS
(TYPICAL)
SWITCHING TIMES (μs)
COLLECTOR CURRENT IC (A)
td(off)
td(on)
tr
tf
VCC = 1650V, VGE = ±15V
RG = 2.5Ω, Tj = 125°C
Inductive load


REVERSE RECOVERY CHARACTERISTICS
OF FREE-WHEEL DIODE
(TYPICAL)
REVERSE RECOVERY TIME trr (μs)
REVERSE RECOVERY CURRENT Irr (A)
EMITTER CURRENT IE (A)
VCC = 1650V, Tj = 125°C
Inductive load
VGE = ±15V, RG = 2.5Ω
Irr
trr


HALF-BRIDGE
SWITCHING ENERGY CHARACTERISTICS
(TYPICAL)
SWITCHING ENERGY (J/P)
CURRENT (A)
VCC = 1650V, VGE = ±15V,
RG = 2.5Ω, Tj = 125°C,
Inductive load
Eon
Eoff
Erec


HALF-BRIDGE
SWITCHING ENERGY CHARACTERISTICS
(TYPICAL)
SWITCHING ENERGY (J/P)
GATE RESISTANCE (Ω)
VCC = 1650V, IC = 800A,
VGE = ±15V, Tj = 125°C,
Inductive load
Eon
Eoff


GATE CHARGE CHARACTERISTICS
(TYPICAL)
GATE-EMITTER VOLTAGE VGE (V)
GATE CHARGE QG (nC)
VCC = 1650V
IC = 800A


TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
NORMALIZED TRANSIENT
THERMAL IMPEDANCE Zth(j – c)
TIME (s)
Single Pulse
TC = 25°C
Rth(j – c)Q = 0.012K/W
Rth(j – c)R = 0.024K/W